

Si Photo-diode Chip—TK0025PDN

1. Scope

- The specification applies to PIN silicon photo-diode chips.
- Type : TK0025PDN.

2. Structure

- PIN planar type.
- Electrode topside (anode) : Aluminum.
- Electrode backside (cathode) : Gold .

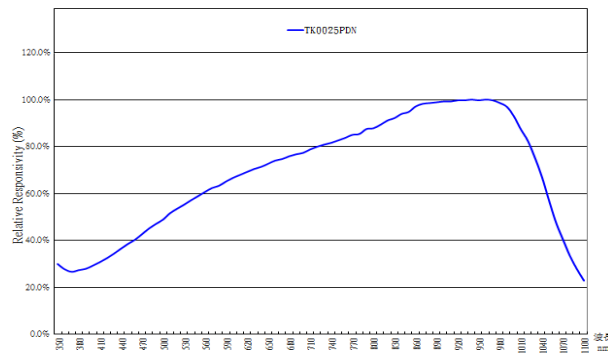
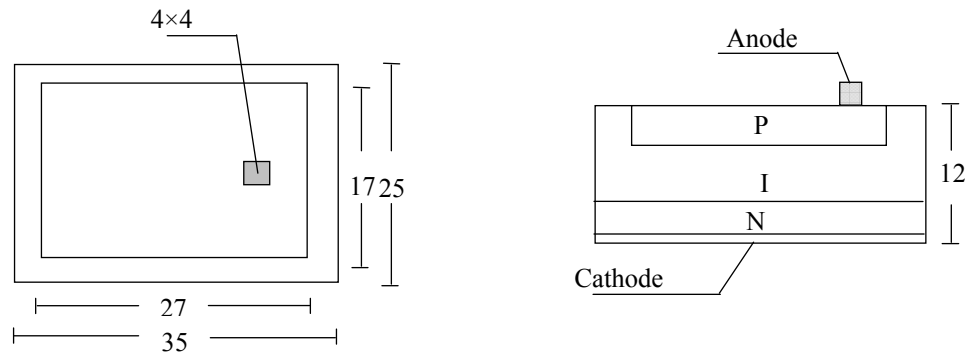
3. Size

- Chip size : 35mil × 25mil ± 1.5mil (0.890mm × 0.640mm ± 0.038mm)
- Thickness : 12mil ± 1mil (0.300mm ± 0.025mm)
- Active area : 27mil × 17mil ± 0.5mil (0.690mm × 0.430mm ± 0.013mm)
- Pad size : 4mil × 4mil ± 0.4mil (0.100mm × 0.100mm ± 0.01mm)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V _F	I _F =10mA, H=0	0.5		1.3	V
Reverse Breakdown Voltage	V _{BR}	I _R =100μA, H=0	35			V
Reverse Dark Current	I _D	V _R =10V, H=0		2	10	nA
Light Current	I _L	V _R =5V, 1mw/cm ² @940nm		10		uA
Peak Sensing Wavelength	λ _p			940		nm
Junction Capacitance	C _J	V _R =3V, H=0, F=1 MHz		1.5		pF



Unit : mil

fig. 1

2016.Mar



TYNTEK Head Office
 TYNTEK Chunan Branch
<http://www.tyntek.com.tw>

Tel : 886-3-5781616

Tel : 886-37-582997

E-mail : service@serv.tyntek.com.tw

Fax : 886-3-5780545

Fax : 886-37-582908